

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	63	jung-Chih near2 tsao Kei-Wei near2 Chen Chi-Wen near2 Liu Shi-Chi near2 Lin Ray near2 Chuang	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/20 10:13
L4	8	2 and pad same (air pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/20 10:14
L3	1	2 and (electroplating plating) and thrust adj pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/20 10:14
L1	1	10/731331	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/20 10:20
L9	92	6 and pressure near3 (different varying varied lower higher less more)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/20 10:28
L10	16	6 and pressure near3 (different varying varied lower higher less more) same (edge peripheral)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/20 10:30
L12	4862	("204" "205").clas. and pressure same (wafer semiconductor workpiece microelectronic micropiece WSID)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/20 11:01
L5	611	("204" "205").clas. and pressure same air same (wafer semiconductor workpiece microelectronic micropiece)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/20 11:01

## EAST Search History

L6	247	5 and (electroplating electropolishing plating polishing planariz\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/20 11:02
L16	17	14 not 11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/20 11:03
L11	9	6 and pressure near3 (different varying varied lower higher less more) same (edge peripheral) same (wafer semiconductor workpiece microelectronic micropiece)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/20 11:03
L17	1315	12 and (electroplating plating)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/20 11:27
L14	26	13 and pressure near3 (different varying varied lower higher less more) same (edge peripheral) same (wafer semiconductor workpiece microelectronic micropiece WSID)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/20 11:28
L18	116	17 and (pressure force pressurized) with (back backside) with (wafer semiconductor workpiece microelectronic micropiece WSID)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/20 11:29
L13	1762	12 and (electroplating electropolishing plating polishing planariz\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/20 13:13
L19	63	(electroplating electropolishing plating) and ("204" "205").clas. and (pressure gas force) with (source ports! inlets! openings!) same (back backside) same (wafer semiconductor workpiece microelectronic micropiece WSID)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/20 13:16

## EAST Search History

L20	16	(electroplating electropolishing plating) and ("204" "205").clas. and (pressure gas force) with (ports! inlets! openings!) same backside same (wafer semiconductor workpiece microelectronic micropiece WSID)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/20 13:17
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